



Diode Module

Features

- A package of series of two diodes
- With high thermal conductivity DBC as the Insulation
- Welding by vacuum welding technology, which provide high reliability

Product Summary

Parameter	Value	Unit
V_{RRM}	1800	V
$I_{F(AV)}(@ T_C = 100^\circ C)$	38	

Applications

- AC converter
- Inverter
- DC motor

Absolute Maximum Ratings (@ $T_C = 25^\circ C$ unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage	$T_{vj} = 25^\circ C$	V_{RRM}	1800	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ C$	V_{RSM}	1900	V
Average forward current	$T_C = 100^\circ C$	$I_{F(AV)}$	380	A
Forward surge current	1/2 cycle, Sine wave, 50Hz $T_{vj} = 25^\circ C$	I_{FSM}	12000	A
I^2t value for fusing		I^2t	720000	A ² s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	

**Electrical Characteristics** (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Peak forward voltage	$I_F=1140\text{A}$, $t_P=380$	V_F			1.60	V
Reverse leakage current	$V_R = V_{RRM}$, $T_{vj} = 25$	I_{RRM}			100	A
	$V_R = V_{RRM}$, $T_{vj} = 150$				100	mA
Threshold voltage	$T_{vj} = 150$, for power loss calculation only	V_{TO}			0.75	V
Dynamic resistance		r_T			0.6	m

Thermal Characteristics (@ $T_C = 1-10 -0 0 9.12 6/1\text{re f } 496.6 36-4.7 (\text{al})15 (\text{c})-4.6 (\text{u})1 189.\text{ID C/MC-10.ur}$)

Typical Electrical & Thermal Characteristics

FIG.1: Forward characteristics (per diode)

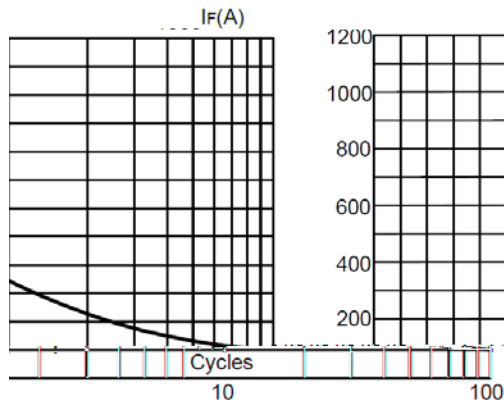


FIG.2: Peak on-state surge current

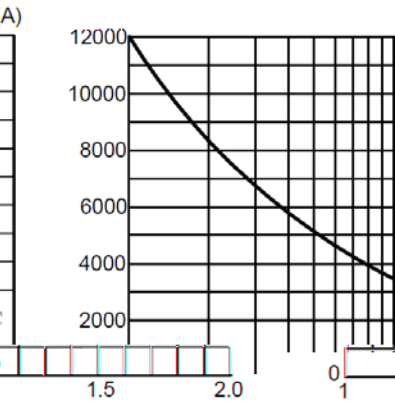


FIG.3: Forward current vs. case temperature

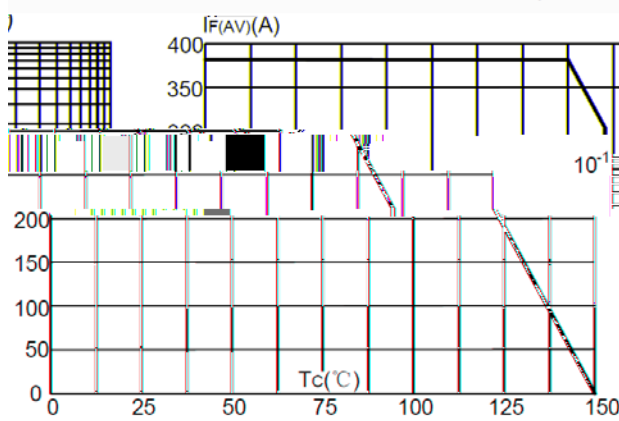
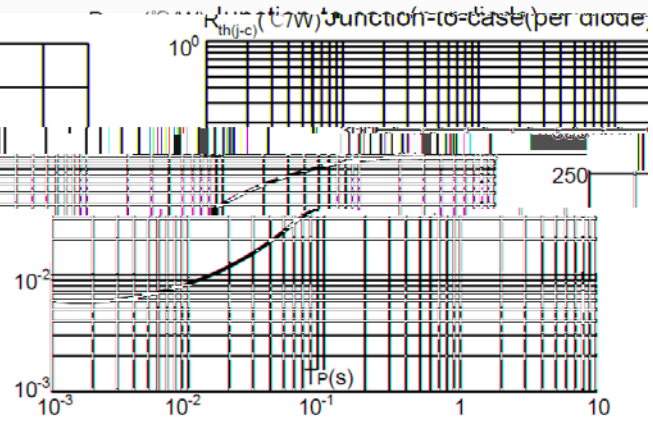
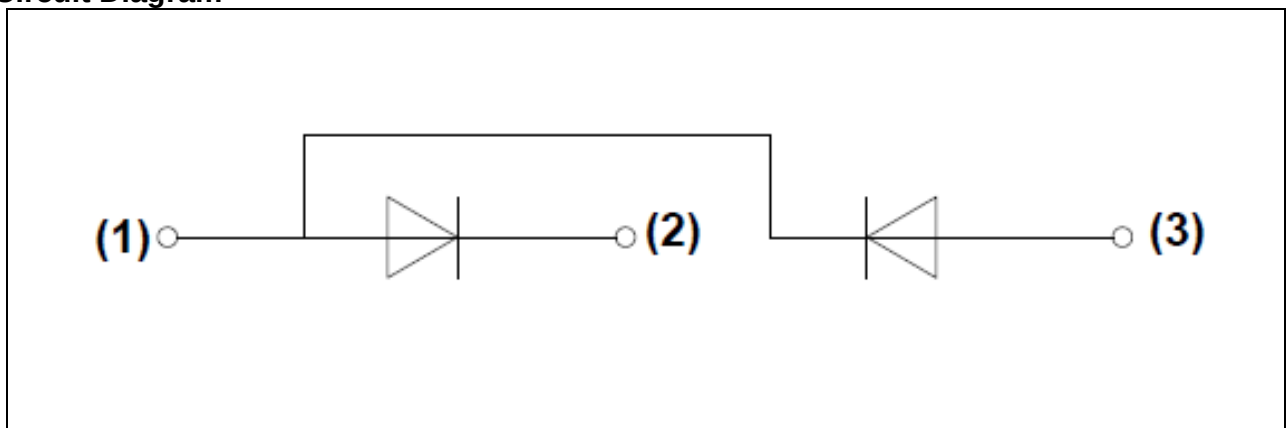
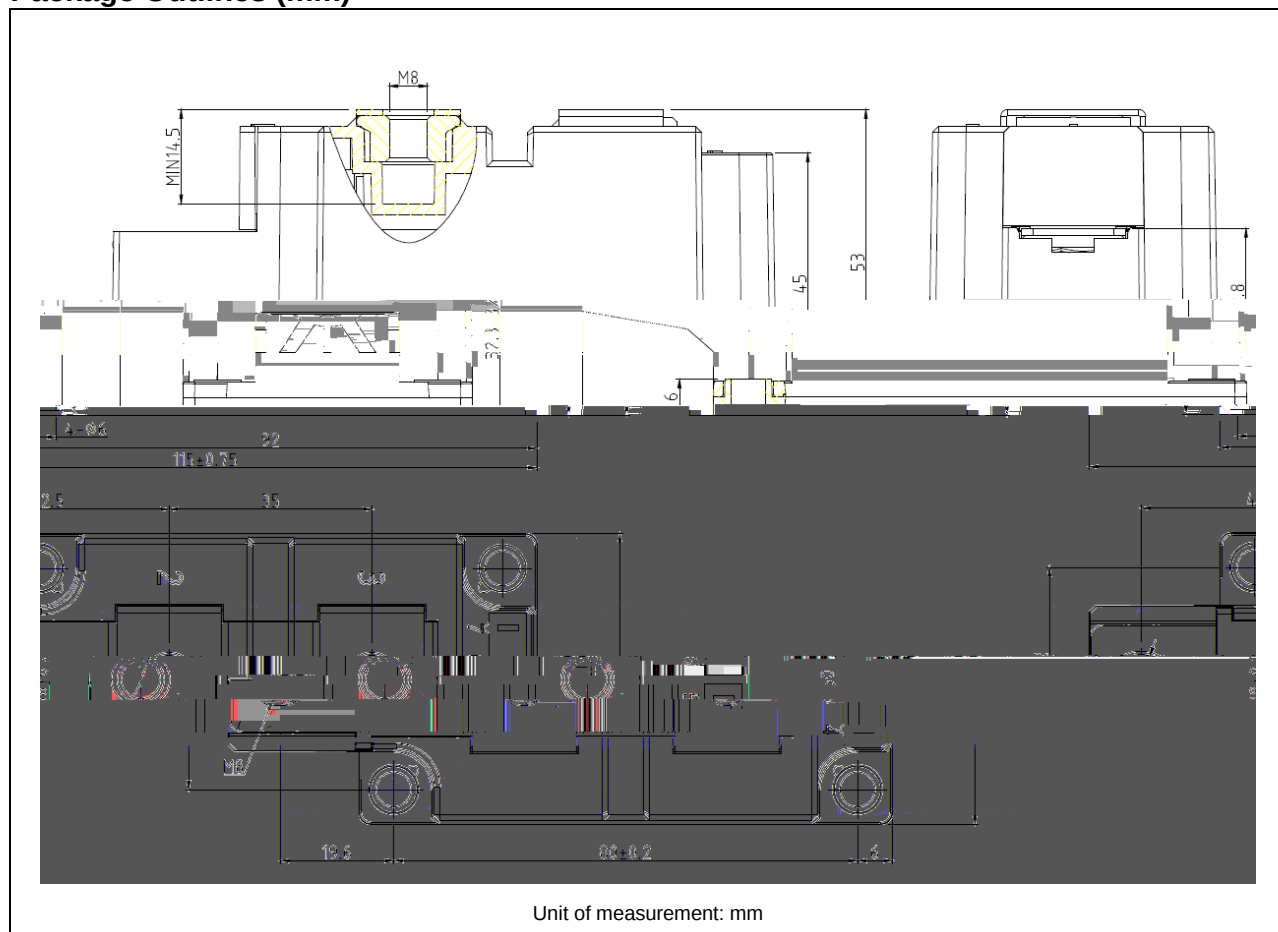


FIG.4: Maximum transient thermal impedance



Circuit Diagram



Package Outlines (mm)




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